

Applied Physics A

Solids and Surfaces

**Volume A 53
1991**

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PHYSICS AND ASTRONOMY CLASSIFICATION SCHEME (PACS)

Shortened version for use in classifying papers for Applied Physics

General

- 02 Mathematical methods in physics
- 06 Measurement science and metrology
- 07 Specific instrumentation
 - 07.60 Optical instruments and techniques, detection of radiation
 - 07.65 Optical spectroscopy and spectrometers
 - 07.75 Mass spectrometers and mass-spectroscopy techniques
 - 07.80 Electron and ion microscopes and spectrometers; techniques
 - 07.85 X-ray and gamma-ray instruments and techniques

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 - E Molecular gas lasers (CO_2 , CO, N_2O , formaldehyde)
 - G Excimer lasers
 - H Atomic, ionic, and other gas lasers
 - M Laser action in liquids and organic dyes
 - P Laser action in semiconductors
 - R Laser action in solid-state lasers
 - T Free-electron lasers
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 - D Laser resonators, cavities, and amplifiers
 - E Laser beam deflection and focusing
 - F Laser beam modulation, mode locking, and tuning
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Solids and Materials

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Visual observation of chemical diffusion in stabilized zirconia.
Appl. Phys. A 53/3, 185-188 (1991) PACS:66.30 71.55
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Unoccupied electronic states in adsorbate systems.
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Quantum crystallites and nonlinear optics.
Appl. Phys. A 53/6, 465-474 (1991) PACS:42.65
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Time-resolved spectroscopy of spontaneous luminescence of $\text{CdS}_x\text{Se}_{1-x}$ quantum dots.
Appl. Phys. A 53/1, 75-80 (1991) PACS:78.47 78.55 81.40
- Chatopadhyay D.:
Two-dimensional electronic transport in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ quantum wells.
Appl. Phys. A 53/1, 35-42 (1991) PACS:72.20H 73.20 73.60
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Role of free carriers in the application of optically detected magnetic resonance for studies of defects in silicon.
Appl. Phys. A 53/2, 130-135 (1991) PACS:76.70H 72.20 71.55
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Investigation of positron reemission holography.
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- Combescot M.:
Theory of dressed-exciton.
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A program for the interactive analysis of positron lifetime spectra on personal computers with the aid of screen graphics.
Appl. Phys. A 53/4, 303-309 (1991) PACS:78.70
- Ehrhardt A., Wetting W., Bett A.:
Transient photoluminescence decay study of minority carrier lifetime in GaAs heteroface solar cell structures.
Appl. Phys. A 53/2, 123-129 (1991) PACS:72.20J 78.55
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Volume and grain boundary diffusion of implanted ^{113}Sn in aluminium.
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Influence of implant dose and target temperature on crystal quality and junction depth of boron-doped silicon layers.
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Properties of silicon-electrolyte junctions and their application to silicon characterization.
Appl. Phys. A 53/1, 8-19 (1991) PACS:82.45 61.70 68.45
- Gleitzer C., Nowotny J., Rekas M.:
Surface and bulk electrical properties of the hematite phase Fe_2O_3 .
Appl. Phys. A 53/4, 310-316 (1991) PACS:68.00 72.00 73.30 73.40
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Iron-aluminum pairs in silicon.
Appl. Phys. A 53/2, 147-154 (1991) PACS:61.70S 61.70 71.55 76.30
- Grünebaum D., Czekalla Th., Stolwijk N.A., Mehrer H., Yonenaga I., Sumino K.:
Diffusion and solubility of zinc in dislocation-free and plastically deformed silicon crystals.
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Relaxation semiconductors: In theory and in practice.
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Luminescence from Ti^{2+} ions in LiF crystals.
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